Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO–92 package which is readily adaptable for use in automatic insertion equipment.

- One-Piece, Injection-Molded Package
- Blocking Voltage to 600 Volts
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Improved Noise Immunity (dv/dt Minimum of 20 V/µsec at 110°C)
- Commutating di/dt of 1.6 Amps/msec at 110°C
- High Surge Current of 8 Amps
- Device Marking: Device Type, e.g., for MAC997A6: MAC7A6, Date Code

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage $(T_J = -40 \text{ to } +110^{\circ}\text{C})(1)$ Sine Wave 50 to 60 Hz, Gate Open MAC997A6,B6 MAC997A8,B8	Vdrm, Vrrm	400 600	Volts
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz $(T_{C} = +50^{\circ}C)$	^I T(RMS)	0.8	Amp
Peak Non–Repetitive Surge Current One Full Cycle, Sine Wave 60 Hz (T _C = 110°C)	ITSM	8.0	Amps
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	.26	A ² s
Peak Gate Voltage (t ≤ 2.0 μs, T _C = +80°C)	V _{GM}	5.0	Volts
Peak Gate Power (t $\leq 2.0 \ \mu$ s, T _C = +80°C)	PGM	5.0	Watts
Average Gate Power ($T_C = 80^{\circ}C, t \le 8.3 \text{ ms}$)	PG(AV)	0.1	Watt
Peak Gate Current (t $\leq 2.0 \ \mu$ s, T _C = +80°C)	IGM	1.0	Amp
Operating Junction Temperature Range	Тj	–40 to +110	°C
Storage Temperature Range	T _{stg}	–40 to +150	°C

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



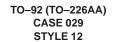
ON Semiconductor

http://onsemi.com

TRIACS 0.8 AMPERE RMS 400 thru 600 VOLTS







PIN ASSIGNMENT		
1 Main Terminal 1		
2	Gate	
3	Main Terminal 2	

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

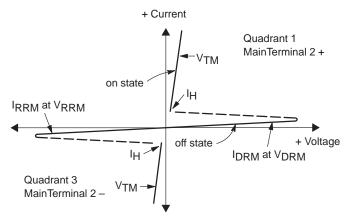
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	75	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	200	°C/W
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	т∟	260	°C

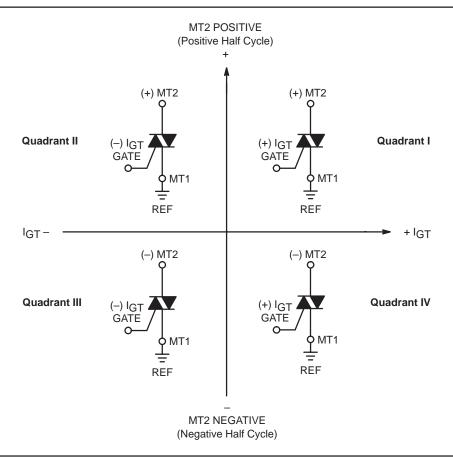
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS					
Peak Repetitive Blocking Current $(V_D = Rated V_{DRM}, V_{RRM}; Gate Open)$ $T_J = 25^{\circ}C$ $T_J = +110^{\circ}C$	I _{DRM} , I _{RRM}	_	_	10 100	μΑ μΑ
ON CHARACTERISTICS			-		-
Peak On–State Voltage (I_{TM} = ± .85 A Peak; Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2.0%)	VTM	-	-	1.9	Volts
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	ΙGΤ			5.0 5.0 7.0 3.0 3.0 3.0 5.0	mA
Latching Current (V_D = 12 V, I_G = 10 mA) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	ι	 	1.6 10.5 1.5 2.5	15 20 15 15	mA
Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	V _{GT}	 	.66 .77 .84 .88	2.0 2.0 2.0 2.5	Volts
Gate Non–Trigger Voltage ($V_D = 12 V$, $R_L = 100 Ohms$, $T_J = 110^{\circ}C$) All Four Quadrants	V _{GD}	0.1	—	_	Volts
Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)	ΙΗ	-	1.5	10	mA
Turn-On Time (V _D = Rated V _{DRM} , I _{TM} = 1.0 A pk, I _G = 25 mA)	tgt	_	2.0	_	μs
DYNAMIC CHARACTERISTICS			-	-	-
Rate of Change of Commutating Current ($V_D = 400 \text{ V}, I_{TM} = .84 \text{ A}, \text{ Commutating dv/dt} = 1.5 \text{ V/}\mu\text{s}, \text{ Gate Open}, T_J = 110^{\circ}\text{C}, f = 250 \text{ Hz}, \text{ with Snubber}$)	di/dt(c)	1.6	—	—	A/ms
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 110°C)	dv/dt	20	60		V/µs
Repetitive Critical Rate of Rise of On–State Current Pulse Width = 20 μ s, IPKmax = 15 A, diG/dt = 1 A/ μ s, f = 60 Hz	di/dt	-	-	10	A/μs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
VTM	Maximum On State Voltage
Ι _Η	Holding Current

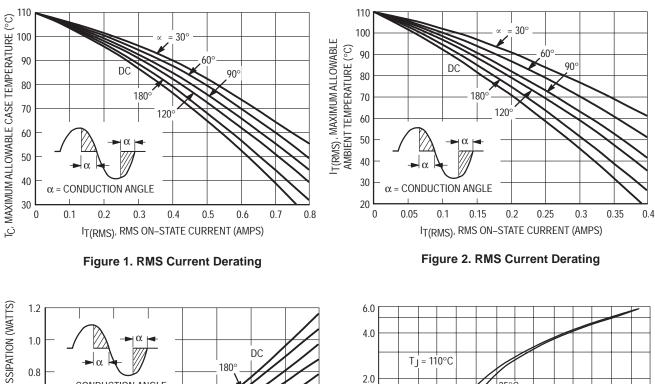




Quadrant Definitions for a Triac

All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



1.0

0.6

0.4

0.2

0.1

0.06

0.04

0.02

0.01

0.006 0.4

1.2

2.0

2.8

3.6

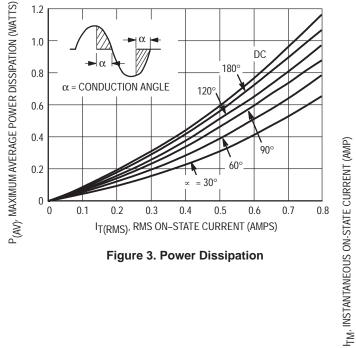
V_{TM}, INSTANTANEOUS ON-STATE VOLTAGE (VOLTS) Figure 4. On–State Characteristics

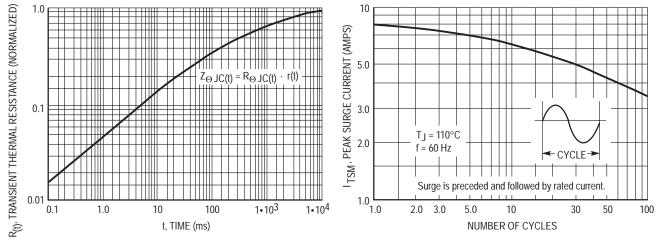
4.4

5.2

6.0

25°Ċ







100

10

0

-40

Q4

Q3

02

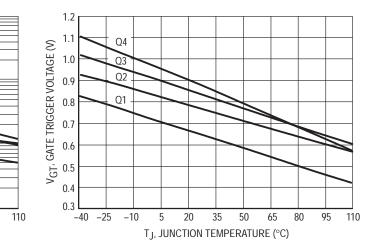
Q1

-10

-25

I_{GT}, GATE TRIGGER CURRENT (mA)







35

TJ, JUNCTION TEMPERATURE (°C)

50

65

80

95

20

5

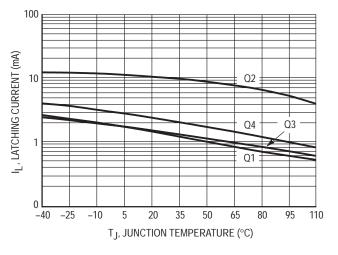
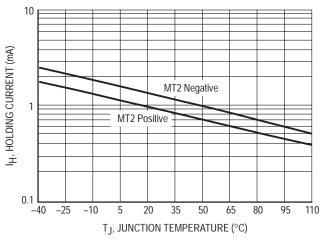
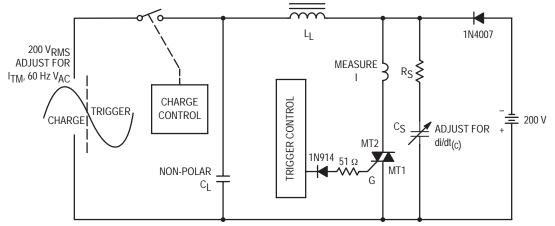


Figure 9. Typical Latching Current versus Junction Temperature

Figure 8. Typical Gate Trigger Voltage versus Junction Temperature







Note: Component values are for verification of rated (di/dt)_C. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)_C

TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

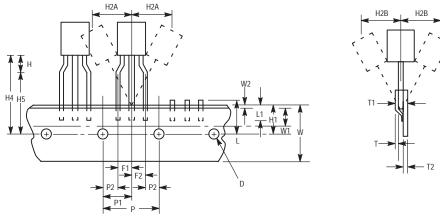


Figure 12. Device Positioning on Tape

		Specification			
		Inches		Millimeter	
Symbol	Item	Min	Max	Min	Max
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.039	0	1.0
H2B	Deflection Front or Rear	0	0.051	0	1.0
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11
L1	Lead Wire Enclosure	0.09842	—	2.5	—
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20
T1	Overall Taped Package Thickness	—	0.0567	—	1.44
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65
W	Carrier Strip Width	0.6889	0.7481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5

NOTES:

1. Maximum alignment deviation between leads not to be greater than 0.2 mm.

2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.

3. Component lead to tape adhesion must meet the pull test requirements.

4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.

5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.

6. No more than 1 consecutive missing component is permitted.

7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.

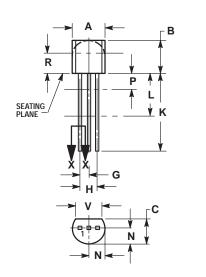
8. Splices will not interfere with the sprocket feed holes.

ORDERING & SHIPPING INFORMATION: MAC97 Series packaging options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO92 Tape Orientation
	MAC997A6RL1, A8RL1 MAC997B6RL1, B8RL1	Radial Tape and Reel (2K/Reel)	Flat side of TO92 and adhesive tape visible
MAC997A6,A8 MAC997B6,B8		Bulk in Box (5K/Box)	N/A, Bulk
MAC997A6RLRP, A8RLRP MAC997B6RLRP, B8RLRP		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO92 and adhesive tape visible

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 **ISSUE AJ**





- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN MAX	
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
К	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2

Notes

Notes

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